



**ELECTRICAL & COMPUTER  
ENGINEERING**  
TEXAS A&M UNIVERSITY

## Lab 10: Characterization of the MOSFET

Kylan Lewis

UIN: 719001131

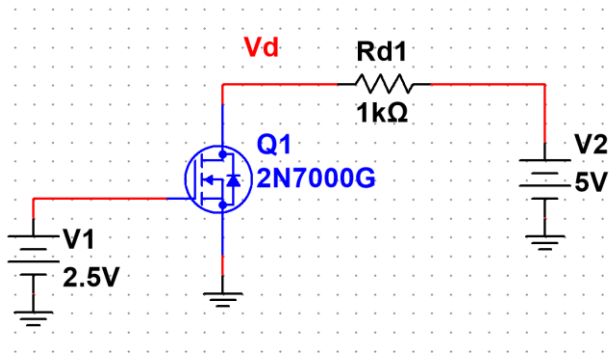
ECEN 325 -501

TA: Jian Shao

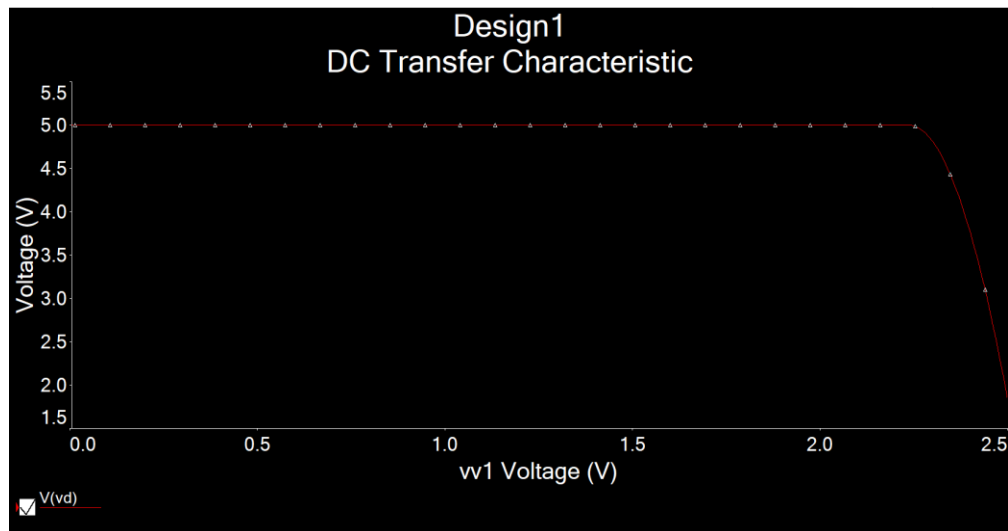
Date: 11/3/2020

## Simulations

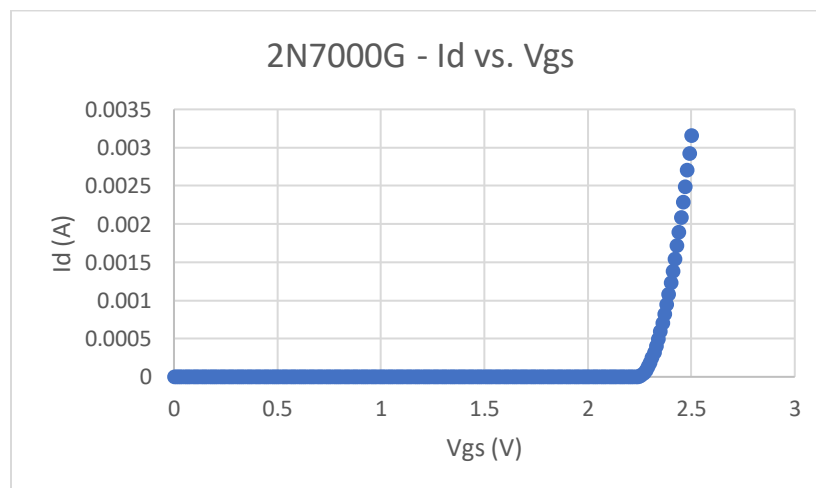
### (1) NMOS using 2N7000G



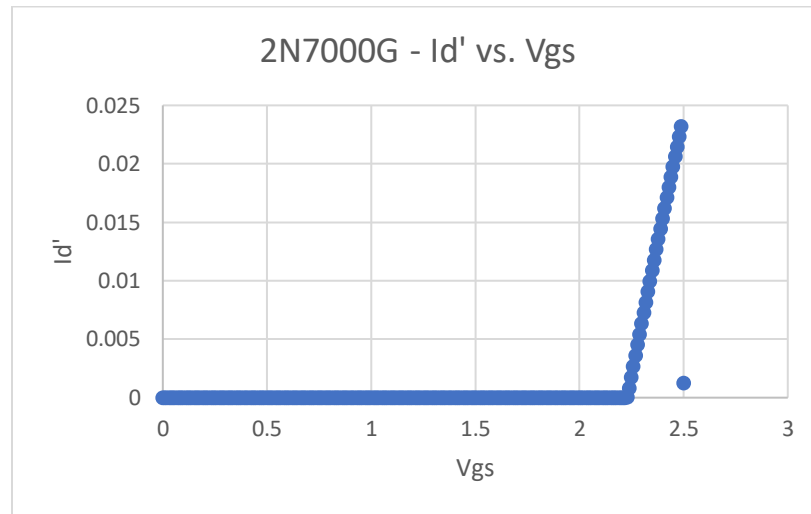
**Figure 1:** Schematic for NMOS using 2N7000G ▲



**Figure 2:** Simulation of NMOS characterization circuit using DC sweep of V1 from 0 to 2.5V, while V2 = 5V ▲



**Figure 3:** Excel plot of NMOS characterization circuit using DC sweep of V1 from 0 to 2.5V, while V2 = 5V, where  $I_d = (5 - V_d)/1000$  ▲

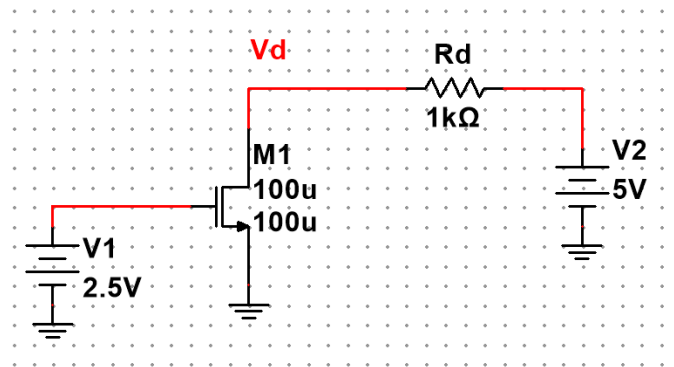


**Figure 4:** Excel plot of NMOS characterization of derivative of Id' vs. Vgs ▲

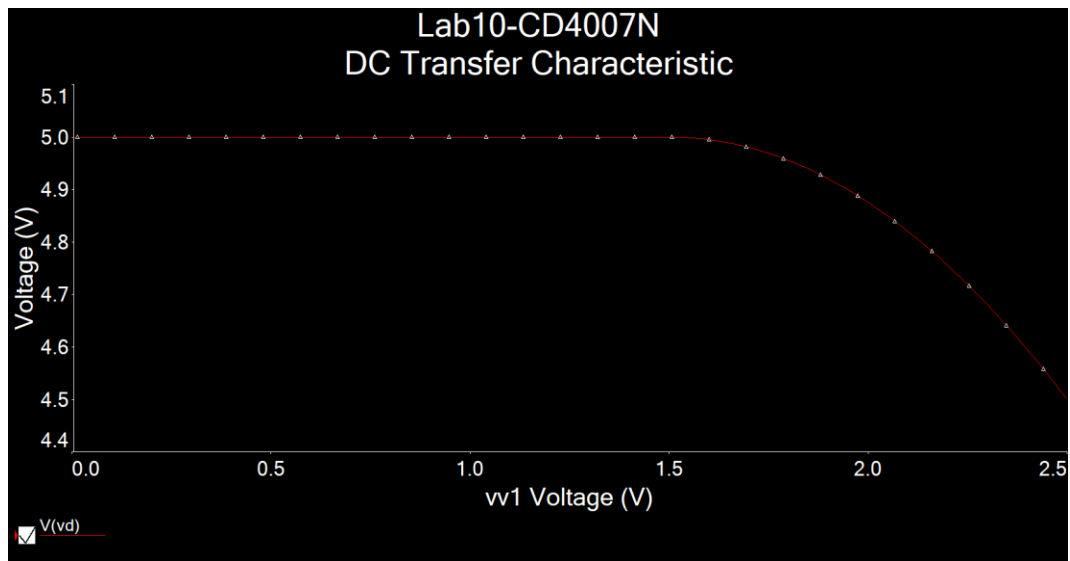
Threshold Voltage  $V_t = 2.23V$

Transconductance parameter =  $(0.023218 - 0)/(2.5 - 2.23) = 0.086$

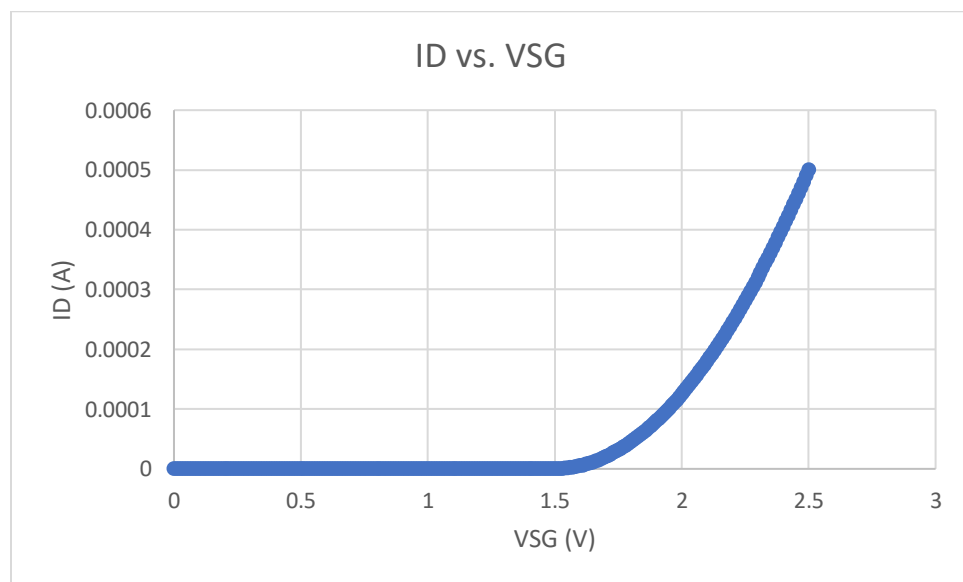
(2) NMOS using CD4007N



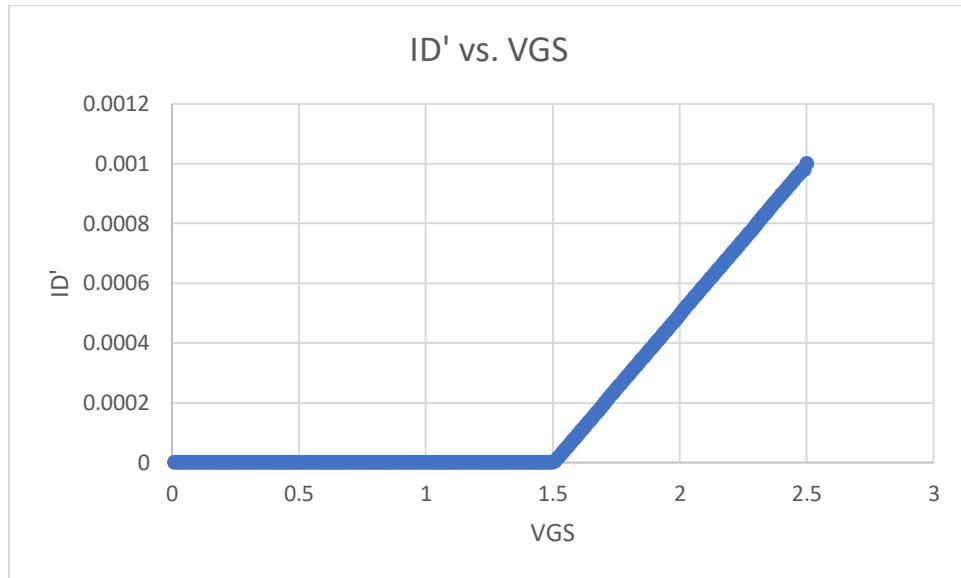
**Figure 5:** Schematic for NMOS using CD4007N ( $\beta = 102\text{mA/V}^2$ ,  $V_{TN} = 2.0V$ ) ▲



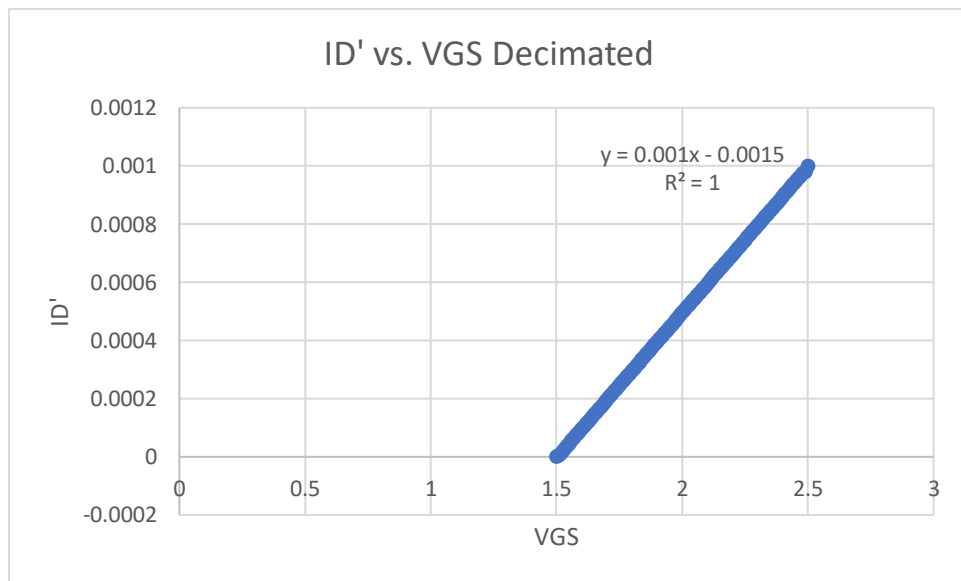
**Figure 6:** Simulation of NMOS characterization circuit using DC sweep of V1 from 0 to 2.5V, while V2 = 5V ▲



**Figure 7:** Excel plot of NMOS characterization circuit using DC sweep of V1 from 0 to 2.5V, while V2 = 5V, where  $I_d = (5 - V_d)/1000$  ▲



**Figure 8-1:** Excel plot of NMOS characterization of derivative of Id' vs. Vgs ▲

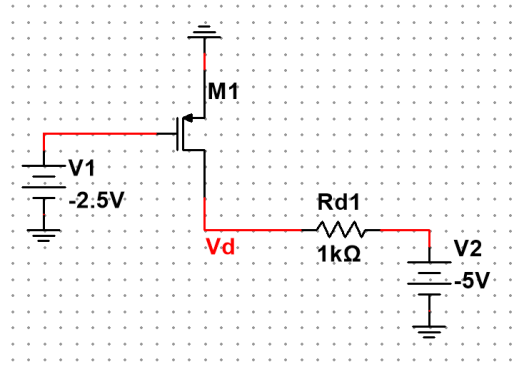


**Figure 8-2:** Excel plot of NMOS characterization of derivative of Id' vs. Vgs Decimated ▲

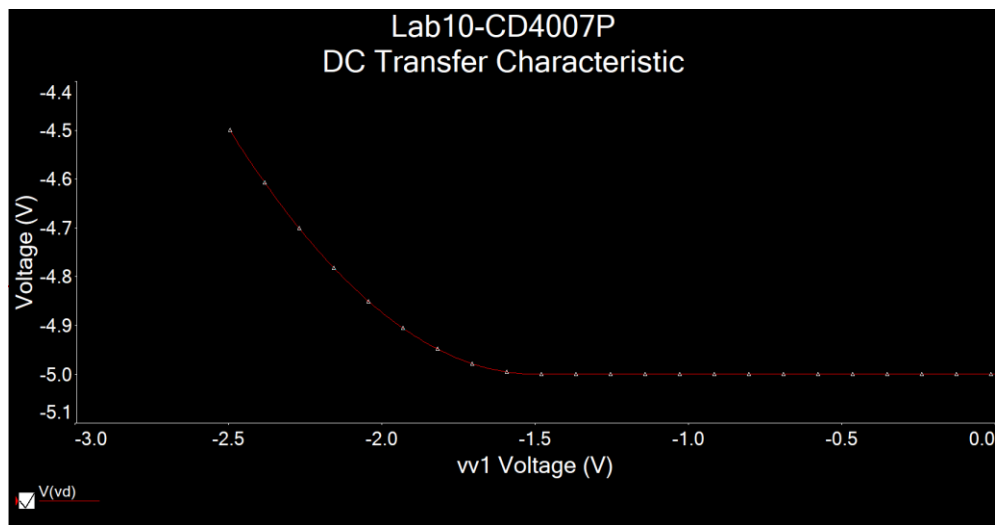
Threshold Voltage  $V_t = 1.5V$

Transconductance parameter =  $0.001A/V^2$

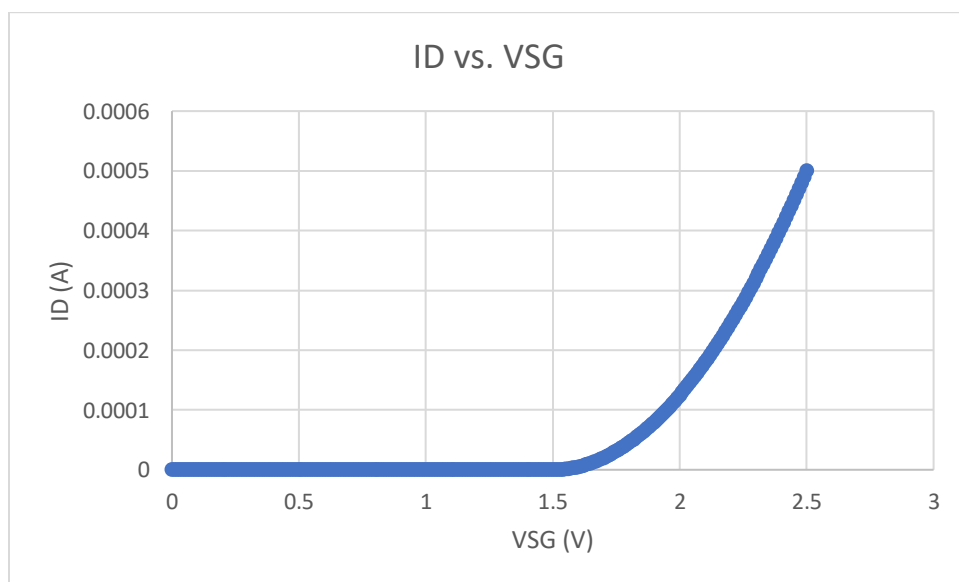
(3) PMOS using CD4007P



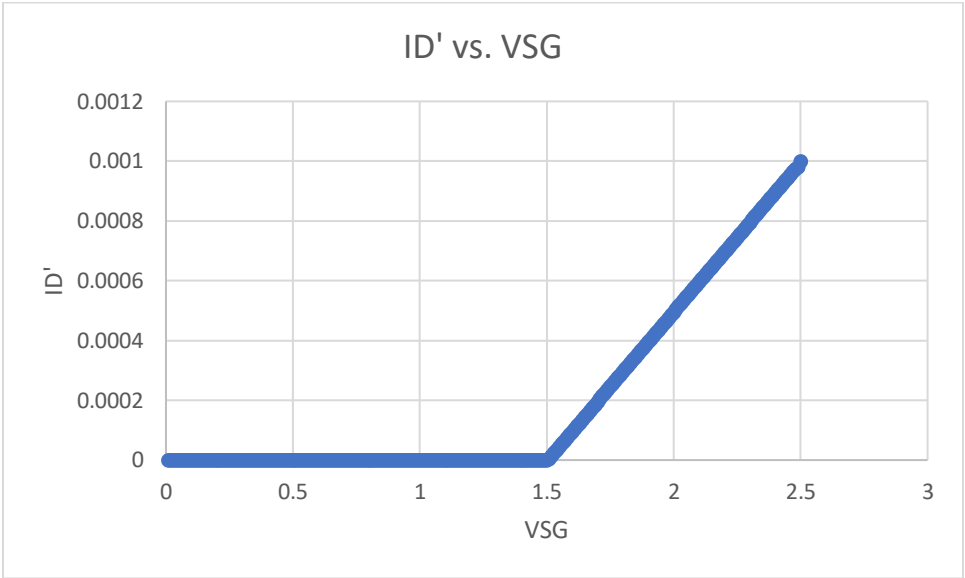
**Figure 9:** Schematic for PMOS using CD4007P ( $\beta=102\text{mA/V}^2$ ,  $V_{TN}=2.0\text{V}$ ) ▲



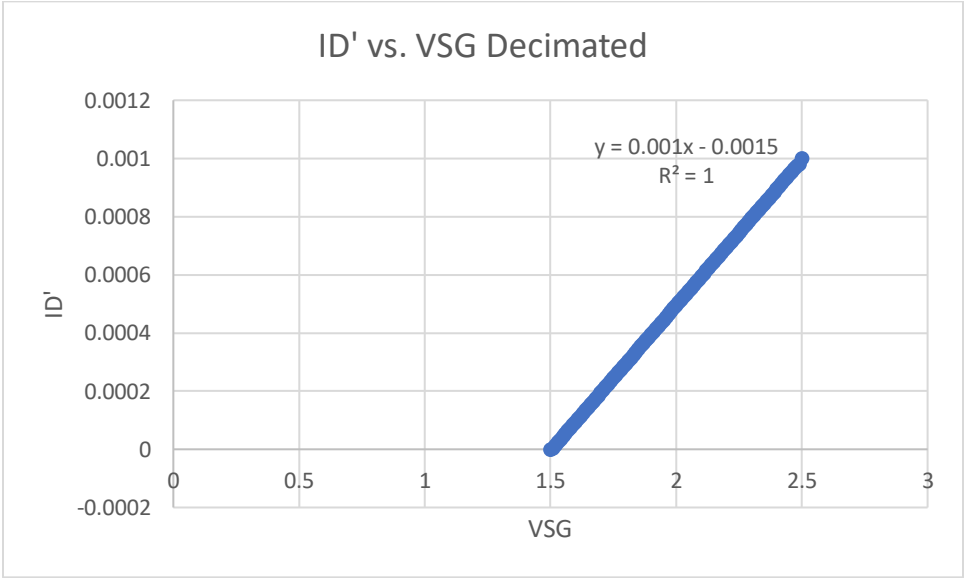
**Figure 10:** Simulation of PMOS characterization circuit using DC sweep of V1 from -2.5 to 0V, while V2 = -5V ▲



**Figure 11:** Excel plot of PMOS characterization circuit using DC sweep of V1 from -2.5 to 0V, while V2 = -5V, where  $I_d = (V_d + 5)/1000$  ▲



**Figure 12-1:** Excel plot of PMOS characterization of derivative of  $I_d'$  vs.  $V_{sg}$  ▲



**Figure 12-2:** Excel plot of PMOS characterization of derivative of  $I_d'$  vs.  $V_{sg}$  Decimated ▲

Threshold Voltage  $V_t = 1.5V$

Transconductance parameter =  $0.001A/V^2$

## TA Question:

My question related to the Lab10 video ( 11:00-21:00 ) is,

Why do we need to apply the decimation technique when we plot the derivative of  $I_d$  as a function of  $V_{GS}$  in the measurement?

We need to apply the decimation technique when we plot the derivative of  $I_d$  as a function of  $V_{GS}$  because the curve is very noisy ( many outliers ). We seek to have a more smooth and filtered plot. In using the decimation technique we need to take a decimation factor “k” which we determined to be 300 and substitute this into the equation as shown below.

$$I_d'(n) = \frac{I_d(n+1) - I_d(n)}{V_{GS}(n+1) - V_{GS}(n)};$$

Substituting in decimation factor  $k$ ,

$$I_d'(n) = \frac{I_d(n+k) - I_d(n)}{V_{GS}(n+k) - V_{GS}(n)}$$

*Note:  $V_{GS}$  is adjusted to the midpoint of  $( I_d(n+k) + I_d(n) )$*